

EAST Search History (25 pp + inv.name searches) ~~1/2~~

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	9815	((257/79) or (257/93) or (257/88) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687) or (257/905) or (257/906) or (257/911)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/09 10:19
L2	0	1 and (IC integrated adj circuit) near4 substrate.clm. and (planari?ed planari?ation planar). clm. and ((mitsuhiko near1 ogihara).in. (fujiwara near1 hiroyuko).in. (sakuta near1 masaki).in. (abiko near1 ichimatsu).in. (oki near1 data).as.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 11:23
L3	0	1 and (IC integrated adj circuit) near20 substrate.clm. and (planari?ed planari?ation planar). clm. and ((mitsuhiko near1 ogihara).in. (fujiwara near1 hiroyuko).in. (sakuta near1 masaki).in. (abiko near1 ichimatsu).in. (oki near1 data).as.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 10:03
L4	1	(IC integrated adj circuit) near20 substrate.clm. and (planari?ed planari?ation planar).clm. and ((mitsuhiko near1 ogihara).in. (fujiwara near1 hiroyuko).in. (sakuta near1 masaki).in. (abiko near1 ichimatsu).in. (oki near1 data).as.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 10:04
L5	1	1 and (light\$1emitting light adj emitting) near20 (printer printing) and (planari?ation planari?ed planar) near10 (thin adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 10:23
L6	4752	((mitsuhiko near1 ogihara).in. (fujiwara near1 hiroyuko).in. (sakuta near1 masaki).in. (abiko near1 ichimatsu).in. (oki near1 data).as.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 10:25
L7	14	((mitsuhiko near1 ogihara).in. (fujiwara near1 hiroyuko).in. (sakuta near1 masaki).in. (abiko near1 ichimatsu).in. (oki near1 data).as.) and (planari?ed planari?ation planar).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 10:53

EAST Search History

L8	6	"936515".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 10:57
L9	4	"970637".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 10:57
L10	3	"998801".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 10:59
L11	0	"11221754".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 11:00
L12	0	"10900281".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 11:00
L13	1	(IC integrated adj circuit) near4 substrate.clm. and (planari?ed planari?ation planar).clm. and ((mitsuhiko near1 ogihara).in. (fujiwara near1 hiroyuki).in. (sakuta near1 masaaki).in. (abiko near1 ichimatsu).in. (oki near1 data).as.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 11:24
S1	4	"743104".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 13:38
S2	1	(US-20040135157-\$).did.	US-PGPUB	OR	OFF	2005/05/24 11:53
S3	0	jp-60206889\$-.did.	US-PGPUB	OR	OFF	2005/05/24 11:54
S4	1	jp-60206889\$-.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 11:58

EAST Search History

S5	2	jp-10063807\$-.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 11:58
S6	152	(257/93).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/11 19:50
S7	209	(257/501).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/11 19:50
S8	360	S6 S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 19:51
S9	127	S8 and (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 19:51
S10	1	S8 and (light adj emitting light-emitting) and ((("without" "no") adj wire adj bond\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 19:54
S11	127	S8 and (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 19:54
S12	34	S8 and (light adj emitting light-emitting) and planar\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 19:54
S13	14	(US-6773943-\$ or US-6692845-\$ or US-6472718-\$ or US-6403985-\$ or US-6339233-\$ or US-6114715-\$ or US-5955747-\$ or US-5866922-\$ or US-5663581-\$ or US-5115284-\$ or US-4984035-\$ or US-4956683-\$ or US-4335501-\$ or US-T979005-\$).did.	USPAT	OR	OFF	2005/06/11 20:11
S14	4	S13 and print\$3	US-PGPUB; USPAT	OR	OFF	2005/06/11 20:33
S15	5349	((257/79) or (257/88) or (257/93) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/12 20:40

EAST Search History

S16	1	S15 and monolithic and substrate near6 integrated adj circuit and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:39
S17	2	S15 and substrate near6 integrated adj circuit and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:43
S18	0	S15 and monolithic and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:43
S19	3	S15 and monolithic and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:45
S20	3	S15 and integrated adj circuit near6 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:46
S21	2	S15 and integrated adj circuit near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:47
S22	2	S15 and (IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:48
S23	17	(IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:55
S24	154	(IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 21:04

EAST Search History

S25	2	("5055907").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 21:26
S26	2	("4755866").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 21:30
S27	6922	(light-emitting light adj emitting LED laser diode) adj array and (integrated adj circuit\$2 IC monolithic\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 21:31
S28	378	(light-emitting light adj emitting LED laser diode) adj array and (integrated adj circuit\$2 IC monolithic\$4) and planariz\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 21:38
S29	189	(light-emitting light adj emitting LED laser adj diode) adj array and (integrated adj circuit\$2 IC monolithic\$4) and planariz\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:22
S30	249	semi-insulating adj substrate.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:23
S31	249	semi-insulating adj substrate.ti. and semi-insulating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:27
S32	3	semi-insulating adj substrate.ti. and semi-insulating near6 defined	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:33
S33	0	(silicon semiconductor semi-insulating) adj substrate near4 "having" near4 (driver integrated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:35
S34	0	(silicon semiconductor semi-insulating) adj substrate near4 "wherein" near4 (driver integrated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:35

EAST Search History

S35	0	(silicon semiconductor semi-insulating) adj substrate near10 "wherein" near4 (driver integrated IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:36
S36	0	(silicon semiconductor semi-insulating) adj substrate near10 "wherein" near10 (driver integrated IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:36
S37	1481	(silicon semiconductor semi-insulating) adj substrate near10 ("in which" "wherein" "having" "within") near10 (driver integrated IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:36
S38	72	(silicon semiconductor semi-insulating) adj substrate near10 ("in which" "wherein" "having" "within") near10 (driver integrated IC) and planariz\$5 and (LED light-emitting light adj emitting laser adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:51
S39	4756	(silicon semiconductor) adj substrate and thin adj2 film and passivation and (integrated adj circuit IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:52
S40	3231	(silicon semiconductor) adj substrate and thin adj2 film and passivation and (integrated adj circuit IC) and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:53
S41	444	(silicon semiconductor) adj substrate and thin adj2 film and passivation adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:56
S42	317	(silicon semiconductor) adj substrate and thin adj2 film and passivation adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 00:02
S43	54	(silicon semiconductor) adj substrate and thin adj2 film and planariz\$5 adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 00:02

EAST Search History

S44	2	"5492851".pn. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:03
S45	2	"4902637".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 16:20
S46	0	(integrated adj circuit adj layer IC adj layer) and (planari?ation planari?e) and (light-emitting light adj emitting diode) adj array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:11
S47	0	(integrated adj circuit adj layer IC adj layer) and (planari?ation planari?e) and (thin adj2 film light-emitting light adj emitting diode) adj array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:12
S48	79	(integrated adj circuit adj layer IC adj layer) and (planari?ation planari?e) and (thin adj2 film light-emitting light adj emitting diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:22
S49	15	(US-20050087817-\$ or US-20040155302-\$ or US-20040155301-\$ or US-20040016976-\$ or US-20040012053-\$ or US-20040007746-\$ or US-20030067043-\$).did. or (US-6903427-\$ or US-6861715-\$ or US-6812488-\$ or US-6717222-\$ or US-6706546-\$ or US-6690845-\$ or US-6684007-\$ or US-6611635-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/06/12 15:22
S50	4	S49 and thin adj film near5 planariz\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:57
S51	0	S49 and thin adj film near5 planariz\$5 and integrated adj circuit adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:25

EAST Search History

S52	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:28
S53	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:45
S54	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:50
S55	0	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and vcsel adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:51
S56	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and device adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:52
S57	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and device adj layer and (planari?e planari?ation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:53
S58	15	S49 and planariz\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:58
S59	0	S49 and planariz\$5 and integrated adj circuit adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:58
S60	15	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:58

EAST Search History

S61	15	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:00
S62	4	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcSEL)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:00
S63	4	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcSEL piezoelectric hall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:01
S64	4	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcSEL piezoelectric hall laser adj diode photodetect\$3 photodiode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:01
S65	15	IC adj layer near6 stack\$3 and (planari?ation planari?e) and (EO LED light-emitting light adj emitting laser diode vcSEL photodiode photodetect\$3 hall adj sensor piezo-electric piezoelectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:24
S66	29	cd-rom near4 diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 18:37
S67	5991	memory adj device and memory adj cell adj array and ((semiconductor silicon) adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:25
S68	2403	memory adj device and memory adj cell adj array.ti,ab,clm. and ((semiconductor silicon) adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:25
S69	1206	memory adj device and memory adj cell adj array.ti,ab,clm. and ((semiconductor silicon) adj substrate).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:25

EAST Search History

S70	687	memory adj device and memory adj cell adj array.ti,ab,clm. and ((semiconductor silicon) adj substrate).ti,ab,clm.	USPAT	OR	ON	2005/06/12 17:26
S71	0	memory adj device and memory adj cell adj array.ti,ab,clm. and ((GaAs) adj substrate).ti,ab,clm.	USPAT	OR	ON	2005/06/12 17:26
S72	0	memory adj device and memory adj cell adj array.ti,ab,clm. and ((GaAs) adj substrate).ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:26
S73	0	memory adj device and memory adj cell adj array.ti,ab,clm. and (GaAs AlGaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:27
S74	0	memory adj device and memory adj cell adj array.ti,ab,clm. and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:27
S75	0	memory adj device and memory adj cell adj array and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:27
S76	45	memory adj device and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:33
S77	5	memory adj device and (SiC) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:34
S78	39	memory adj device and (GaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:34
S79	12	config-dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:01

EAST Search History

S80	8	source near6 common adj ground and memory adj array.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:11
S81	31389	CD-ROM and Dvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:12
S82	2	CD-ROM and Dvd and memory adj array and laser adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:13
S83	2	"5696714".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:13
S84	5611	((257/79) or (257/88) or (257/93) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687) or (257/905) or (257/906) or (257/911)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/12 20:40
S85	0	S84 and (planari?ation planari?e) and (Si silicon semiconductor) adj thin adj film and (integrated adj circuit IC) adj2 (layer) and (light-emitting light adj emitting laser adj diode photodiode photodetect\$3 hall adj sensor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 20:42
S86	4649	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 15:59
S87	806	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:01

EAST Search History

S88	6	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and oled	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:03
S89	2	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and oled and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:04
S90	0	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and (electroluminescent adj layer) and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:05
S91	0	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and (electroluminescent adj layer) and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:05

EAST Search History

S92	9	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and light-emitting and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:06
S93	12	integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and (light adj emitting light-emitting) and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 16:06
S94	1614	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:07
S95	1097	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:08
S96	1098	(planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:08

EAST Search History

S97	534	(planari?e planari?ed planari?ation planari?ing) near2 (region layer) and (planari?e planari?ed planari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:09
S98	287	(planari?e planari?ed planari?ation planari?ing) near2 (region layer) and (planari?e planari?ed planari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:10
S99	196	(planari?e planari?ed planari?ation planari?ing) near2 (region layer) and (planari?e planari?ed planari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:10
S100	15	(planari?e planari?ed planari?ation planari?ing) near2 (region layer) and (planari?e planari?ed planari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:13
S101	22	(planari?e planari?ed planari?ation planari?ing) near2 (region layer) and (planari?e planari?ed planari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:16

EAST Search History

S10 2	32	(planari?e planari?ed planari?ation planari?ing planar) near2 (region layer) and (planari?e planari?ed planari?ation planari?ing planar) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:37
S10 3	13	(first second) near1 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:41
S10 4	210	(first second) near1 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:45
S10 5	62	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:47

EAST Search History

S10 6	2	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:48
S10 7	2	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and (tft thin adj film otft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:50
S10 8	2	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and (tft thin adj film otft silicon-on-insulator "soi")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 17:51
S10 9	14	first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and (tft thin adj film otft silicon-on-insulator "soi")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 18:31

EAST Search History

S11 0	2	("20030067043").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 18:33
S11 1	19	"5492851"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 18:34
S11 2	2	("5492851").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 18:34
S11 3	2	S112	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 18:42
S11 4	2	("20050199924").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 19:02
S11 5	2	("20050052823").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 19:13
S11 6	509	(257/752).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 19:38
S11 7	22	S116 and (thin adj film adj transistor tft otft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/23 19:38
S11 8	22	S116 and (thin adj film adj transistor tft otft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 19:40
S11 9	19	S116 and (thin adj film adj transistor tft otft) and (planar planari?e planari?ed planari?ation flat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 19:41

EAST Search History

S12 0	537	(silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari?ing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 08:16
S12 1	0	(silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari?ing) and intergated adj circuit and (silicon semiconductor) near1 substrate and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 08:17
S12 2	184	(silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari?ing) and integrated adj circuit and (silicon semiconductor) near1 substrate and @ad<"20021225"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 08:18
S12 3	139	(silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari?ing) and integrated adj circuit and (silicon semiconductor) near1 substrate and @ad<"20021225"	USPAT; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 08:26
S12 4	1	(US-20040135157-\$).did.	US-PGPUB	OR	OFF	2006/02/24 08:41
S12 5	1	S124 and raised adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 09:40
S12 6	0	zhang.in. and stacked near4 tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 09:41
S12 7	0	semiconductor adj energy.in. and stacked near4 tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 09:41
S12 8	0	semiconductor adj energy.in. and stack\$3 near4 tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:42

EAST Search History

S12 9	0	semiconductor adj energy.in. and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:42
S13 0	5688	semiconductor adj energy.as. and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:42
S13 1	21	semiconductor adj energy.as. and tft near4 stack\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:44
S13 2	457	tft near4 stack\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 09:44
S13 3	64	tft near4 stack\$4.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 10:38
S13 4	28	tft near4 stack\$4.ti,ab,clm. and (silicon semiconductor) near4 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 10:38
S13 5	1	(US-20040135157-\$).did.	US-PGPUB	OR	OFF	2006/02/24 15:03
S13 6	9	optical adj print adj head and (tft active adj matrix adj display)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:07
S13 7	7	optical adj print adj head and (active adj matrix)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:09
S13 8	5	optical adj print adj head and (active adj matrix) and print adj head and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:09

EAST Search History

S13 9	0	optical adj print adj head and (active adj matrix) and print adj head near20 tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:09
S14 0	0	optical adj print adj head and (active adj matrix) and print adj head same tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:09
S14 1	7	optical adj print adj head and (active adj matrix) and print adj head	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:12
S14 2	48	print adj head and ((active adj matrix) near20 tft) and print adj head	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:13
S14 3	1	print adj head and ((active adj matrix) near20 tft) near20 (print adj head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:14
S14 4	1	print\$3 adj head and ((active adj matrix) near20 tft) near20 (print\$3 adj head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:16
S14 5	0	print\$3 adj head and ((matrix adj2 display) near20 tft) near20 (print\$3 adj head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:16
S14 6	1	print\$3 adj head and ((matrix) near20 tft) near20 (print\$3 adj head)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:28

EAST Search History

S14 7	0	09-045930\$-\$ did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:28
S14 8	0	"09045930"\$-\$ did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:28
S14 9	2	jp-09045930\$-\$ did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 19:43
S15 0	0	"6255705".pn. and print\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:41
S15 1	1	(US-20040135157-\$).did.	US-PGPUB	OR	OFF	2006/02/24 17:21
S15 2	1	S151 and common	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 17:21
S15 3	1	S151 and common	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 17:21

EAST Search History

S15 4	61	(US-20030141504-\$ or US-20020163000-\$ or US-20040135157-\$ or US-20030067043-\$ or US-20020168856-\$ or US-20040012053-\$ or US-20040007746-\$ or US-20040130015-\$ or US-20040094770-\$ or US-20030102473-\$ or US-20040125197-\$ or US-20040166659-\$ or US-20030170934-\$ or US-20040089939-\$ or US-20050100279-\$ or US-20030133668-\$ or US-20040155302-\$ or US-20040155301-\$ or US-20050087817-\$ or US-20040016976-\$ or US-20020061040-\$).did. or (US-6828227-\$ or US-5492851-\$ or US-5031187-\$ or US-6692837-\$ or US-6476485-\$ or US-6307264-\$ or US-4902637-\$ or US-6876008-\$ or US-6773943-\$ or US-6692845-\$ or US-6472718-\$ or US-6403985-\$ or US-6339233-\$ or US-6114715-\$ or US-5955747-\$ or US-5866922-\$ or US-5663581-\$ or US-5115284-\$ or US-4984035-\$ or US-4956683-\$ or US-4335501-\$ or US-T979005-\$ or US-5055907-\$ or US-5789766-\$ or US-6410960-\$ or US-6903427-\$).did. or (US-6849877-\$ or US-6861715-\$ or US-6812488-\$ or US-6717222-\$ or US-6706546-\$ or US-6690845-\$ or US-6684007-\$ or US-6611635-\$ or US-6222755-\$ or US-5696714-\$ or US-6380572-\$).did. or (JP-10063807-\$ or JP-61102767-\$).did. or (JP-10063807-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2006/02/24 17:24
S15 5	1	S154 and common near2 (source drain gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 17:25

EAST Search History

S15 6	1	S154 and gate adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 18:04
S15 7	40	tft and active adj matrix and compound adj semiconductor near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 18:05
S15 8	18	tft and active adj matrix and compound adj semiconductor near1 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 18:15
S15 9	0	tft and active adj matrix and compound adj semiconductor near1 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 18:16
S16 0	0	tft and active adj matrix and (gan gaas compound adj semiconductor) near1 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 18:16
S16 1	14	tft and (gan gaas compound adj semiconductor) near5 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 18:17
S16 2	2	("20030067043").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/24 19:43
S16 3	7	"734294".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 13:52
S16 4	2	("5838608").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:34
S16 5	19	"5492851"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:34

EAST Search History

S16 6	2	("5492851").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:41
S16 7	0	("743294.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:41
S16 8	6	"743294".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:41
S16 9	7	"734294".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 14:42
S17 0	2	"20040175887".pn..	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 15:28
S17 1	2	("20030067043").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 16:03
S17 2	8789	((257/79) or (257/93) or (257/88) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687) or (257/905) or (257/906) or (257/911)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/25 16:04
S17 3	0	S172 and planarized adj (layer region film).clm. and (integrated adj circuit IC).clm. and (semiconductor silicon gan gaas sige) near2 substrate.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 16:06
S17 4	0	S172 and planarized near4 (layer region film).clm. and (integrated adj circuit IC).clm. and (semiconductor silicon gan gaas sige) near2 substrate.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 16:06

EAST Search History

S17 5	1	S172 and planarized near4 (layer region film).ti,ab,clm. and (integrated adj circuit IC).ti,ab, clm. and (semiconductor silicon gan gaas sige) near2 substrate.ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/25 16:06
S17 6	2	("6255705").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 20:03
S17 7	5	"384014".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 20:06
S17 8	2	("20040173808").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/08 20:06
S17 9	8	"561564"	DERWENT	OR	OFF	2006/12/08 20:07
S18 0	2	("20030067043").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/09 00:10


PALM INTRANET

 Day : Saturday
 Date: 12/9/2006
 Time: 10:51:16
Inventor Name Search Result

Your Search was:

Last Name = OGIIHARA

First Name = MITSUHIKO

Application#	Patent#	Status	Date Filed	Title	Inventor Name
08326498	5523590	150	10/20/1994	LED ARRAY WITH INSULATING FILMS	OGIIHARA, MITSUHIKO
08326499	5530268	150	10/20/1994	LIGHT-EMITTING DIODE ARRAY WITH ANTI-REFLECTION COATING PROVIDING REDUCED INTERNAL REFLECTION	OGIIHARA, MITSUHIKO
08501649 <i>ab.</i>	Not Issued	166	07/12/1995	END FACET LIGHT EMITTING TYPE LIGHT EMITTING DIODE, MANUFACTURING METHOD FOR AN END FACET LIGHT EMITTING TYPE LIGHT EMITTING DEVICE AND MEASURING METHOD FOR THE SAME	OGIIHARA, MITSUHIKO
08588890	5700714	150	01/19/1996	DIFFUSION MASK AND FABRICATION METHOD FOR FORMING PN-JUNCTION ELEMENTS IN A COMPOUND SEMICONDUCTOR SUBSTRATE	OGIIHARA, MITSUHIKO
08611410	5733689	150	03/06/1996	LED ARRAY FABRICATION PROCESS WITH IMPROVED UNIFORMITY	OGIIHARA, MITSUHIKO
08763860	5821567	150	12/11/1996	HIGH-RESOLUTION LIGHT-SENSING AND LIGHT-EMITTING DIODE ARRAY	OGIIHARA, MITSUHIKO
08900064	5955747	150	07/23/1997	HIGH-DENSITY LIGHT-EMITTING-DIODE ARRAY UTILIZING A PLURALITY OF ISOLATION CHANNELS	OGIIHARA, MITSUHIKO
08923816	6054724	150	09/04/1997	LIGHT-EMITTING DIODE, LIGHT-EMITTING DIODE ARRAY	OGIIHARA, MITSUHIKO
08924832	5917227	150	09/05/1997	LIGHT-EMITTING-DIODE ARRAY AND LIGHT-EMITTING-DIODE ELEMENT	OGIIHARA, MITSUHIKO
08929759	5997152	150	09/15/1997	LIGHT EMITTING ELEMENT	OGIIHARA,

				MODULE AND PRINTER HEAD USING THE SAME	MITSUHIKO
<u>08929760</u> <i>ab.</i>	Not Issued	164	09/15/1997	A LIGHT EMITTING ELEMENT MODULE WITH A PARALLELOGRAM SHAPED CHIP AND A STAGGERED CHIP ARRAY	OGIHARA, MITSUHIKO
<u>08942302</u>	5955748	150	10/01/1997	END FACE LIGHT EMITTING TYPE LIGHT EMITTING DIODE	OGIHARA, MITSUHIKO
<u>08944196</u> <i>ab.</i>	Not Issued	161	10/03/1997	DIFFUSION MASK AND FABRICATION METHOD FOR FORMING PN-JUNCTION ELEMENTS IN A COMPOUND SEMICONDUCTION SUBSTRATE	OGIHARA, MITSUHIKO
<u>08997735</u>	5869221	150	12/24/1997	METHOD OF FABRICATING AN LED ARRAY	OGIHARA, MITSUHIKO
<u>09031534</u>	5972729	150	02/27/1998	METHOD OF MANUFACTURING LIGHT-RECEIVING/EMITTING DIODE ARRAY CHIP	OGIHARA, MITSUHIKO
<u>09040450</u>	6211537	150	03/18/1998	LED ARRAY	OGIHARA, MITSUHIKO
<u>09057611</u>	6064418	150	04/09/1998	LED ARRAY, PRINT HEAD, AND ELECTROPHOTOGRAPHIC PRINTER	OGIHARA, MITSUHIKO
<u>09084324</u>	6388696	150	05/27/1998	LED ARRAY, AND LED PRINTER HEAD	OGIHARA, MITSUHIKO
<u>09089093</u>	6222208	150	06/02/1998	LIGHT-EMITTING DIODE AND LIGHT-EMITTING DIODE ARRAY	OGIHARA, MITSUHIKO
<u>09093609</u>	6180961	150	06/09/1998	LIGHT EMITTING SEMICONDUCTOR DEVICE WITH STACKED STRUCTURE	OGIHARA, MITSUHIKO
<u>09106088</u>	6172701	150	06/29/1998	LIGHT EMITTING ELEMENT ARRAY CHIP, LIGHT EMITTING ELEMENT ARRAY DRIVE IC AND PRINT HEAD	OGIHARA, MITSUHIKO
<u>09128856</u>	6133588	150	08/04/1998	LIGHT-EMITTING ELEMENT, ARRAY, AND FABRICATION METHOD WITH SEPARATE LIGHT-EMITTING AND CURRENT-CONDUCTING DIFFUSION AREAS	OGIHARA, MITSUHIKO
<u>09137073</u>	6136627	150	08/20/1998	HIGH-RESOLUTION LIGHT-SENSING AND LIGHT-EMITTING DIODE ARRAY AND FABRICATION METHOD THEREOF	OGIHARA, MITSUHIKO

<u>09145278</u>	6063644	150	09/02/1998	LIGHT-EMITTING ELEMENT AND ARRAY WITH ETCHED SURFACE, AND FABRICATION METHOD THEREOF	OGIHARA, MITSUHIKO
<u>09291069</u>	6407410	150	04/14/1999	SEMICONDUCTOR OPTICAL DEVICE	OGIHARA, MITSUHIKO
<u>09302472</u>	6163036	150	04/30/1999	LIGHT EMITTING ELEMENT MODULE WITH A PARALLELOGRAM-SHAPED CHIP AND A STAGGERED CHIP ARRAY	OGIHARA, MITSUHIKO
<u>09312848</u>	6313483	150	05/17/1999	LIGHT-EMITTING SEMICONDUCTOR DEVICE WITH REDUCED NONRADIATIVE RECOMBINATION	OGIHARA, MITSUHIKO
<u>09328265</u>	6054726	150	06/17/1999	LIGHT-EMITTING SEMICONDUCTOR DEVICE WITH PLANAR STRUCTURE	OGIHARA, MITSUHIKO
<u>09329804</u>	6271051	150	06/10/1999	LIGHT-EMITTING DIODE, LIGHT-EMITTING DIODE ARRAY, AND METHOD OF THEIR FABRICATION	OGIHARA, MITSUHIKO
<u>09348562</u>	6384429	150	07/07/1999	LIGHT-EMITTING SEMICONDUCTOR DEVICE WITH REDUCED OBSTRUCTIONS TO LIGHT EMISSION	OGIHARA, MITSUHIKO
<u>09359789</u>	6190935	150	07/26/1999	LOW-COST, HIGH-DENSITY LIGHT-EMITTING-DIODE ARRAY AND FABRICATION METHOD THEREOF	OGIHARA, MITSUHIKO
<u>09595248</u>	6583446	150	06/15/2000	ARRAY OF LIGHT-EMITTING ELEMENTS AND EMISSION-ALTERING ELEMENTS	OGIHARA, MITSUHIKO
<u>09750299</u>	6563138	150	12/29/2000	LOW-COST, HIGH-DENSITY LIGHT-EMITTING-DIODE ARRAY AND FABRICATION METHOD THEREOF	OGIHARA, MITSUHIKO
<u>10123354</u>	6621105	150	04/16/2002	ARRAY OF LIGHT-EMITTING ELEMENTS WITH MULTILAYER WIRING	OGIHARA, MITSUHIKO
<u>10253730</u>	6717184	150	09/23/2002	LIGHT-EMITTING ELEMENT ARRAY	OGIHARA, MITSUHIKO
<u>10322740</u>	6762437	150	12/19/2002	LIGHT EMITTING SEMICONDUCTOR DEVICE	OGIHARA, MITSUHIKO
<u>10701622</u>	Not Issued	93	11/06/2003	SEMICONDUCTOR APPARATUS WITH THIN SEMICONDUCTOR	OGIHARA, MITSUHIKO

				FILM	
<u>10705895</u> Mo D P	Not Issued	41	11/13/2003	Combined semiconductor apparatus with thin semiconductor films	OGIHARA, MITSUHIKO
<u>10716601</u>	6790695	150	11/20/2003	SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME	OGIHARA, MITSUHIKO
<u>10725078</u>	6881978	150	12/02/2003	SEMICONDUCTOR EPITAXIAL STRUCTURE AND SEMICONDUCTOR LIGHT-EMITTING DEVICE	OGIHARA, MITSUHIKO
<u>10734620</u>	7135708	150	12/15/2003	SEMICONDUCTOR APPARATUS HAVING CONDUCTIVE LAYERS AND SEMICONDUCTOR THIN FILMS	OGIHARA, MITSUHIKO
<u>10734676</u>	7122834	150	12/15/2003	SEMICONDUCTOR APPARATUS HAVING ADHESION LAYER AND SEMICONDUCTOR THIN FILM	OGIHARA, MITSUHIKO
<u>10743104</u> aurs	Not Issued	71	12/23/2003	Combined semiconductor apparatus with semiconductor thin film	OGIHARA, MITSUHIKO
<u>10870142</u>	6913985	150	06/18/2004	METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE	OGIHARA, MITSUHIKO
<u>10900281</u> Mo D P	Not Issued	80	07/28/2004	Semiconductor light-emitting device	OGIHARA, MITSUHIKO
<u>10926890</u>	7061113	150	08/26/2004	SEMICONDUCTOR APPARATUS, LED HEAD, AND IMAGE FORMING APPARATUS	OGIHARA, MITSUHIKO
<u>10936515</u> no D P	Not Issued	40	09/09/2004	Combined semiconductor device, LED print head, and image forming apparatus	OGIHARA, MITSUHIKO
<u>10970637</u> Mo D P	Not Issued	71	10/21/2004	Semiconductor device, LED print head and image-forming apparatus using same, and method of manufacturing semiconductor device	OGIHARA, MITSUHIKO
<u>10998801</u> no D P	Not Issued	71	11/30/2004	Semiconductor apparatus, LED print head, and printer	OGIHARA, MITSUHIKO
<u>11221754</u> (see ePon: Mo D P)	Not Issued	30	09/09/2005	Semiconductor composite device, method for manufacturing the semiconductor composite device, LED head that employs the semiconductor composite device, and image forming apparatus that employs the LED head	OGIHARA, MITSUHIKO

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ogihara

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mitsuhiko


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Your Search was:

Last Name = FUJIWARA

First Name = HIROYUKI

Application#	Patent#	Status	Date Filed	Title	Inventor Name
06136316	4362480	150	04/01/1980	ROTARY ROTARY BANE PUMP MADE OF SPECIFIC MATERIALS	FUJIWARA, HIROYUKI
07153677	4898943	150	02/08/1988	TRICYCLIC TRIAZOLOPYRIMIDINE DERIVATIVES	FUJIWARA, HIROYUKI
07459510	Not Issued	166	01/02/1990	TRICYCLIC TRIAZOLOPYRIMIDINE DERIVATIVES	FUJIWARA, HIROYUKI
07698174	Not Issued	166	05/06/1991	TRICYCLIC TRIAZOLOPYRIMIDINE DERIVATIVES	FUJIWARA, HIROYUKI
07823570	5299902	150	01/21/1992	CHIP-TYPE ELECTRONIC ELEMENT SUPPLYING APPARATUS	FUJIWARA, HIROYUKI
07830865	Not Issued	168	02/04/1992	TRICYCLIC TRIAZOLOPYRIMIDINE DERIVATIVES	FUJIWARA, HIROYUKI
07972084	Not Issued	161	11/05/1992	TRICYCLIC TRIAZOLOPYRIMIDINE DERIVATIVES	FUJIWARA, HIROYUKI
08164713	5525023	150	12/10/1993	CHIP COMPONENT SUPPLY APPARATUS	FUJIWARA, HIROYUKI
08501649 <i>No DP</i>	Not Issued	166	07/12/1995	END FACET LIGHT EMITTING TYPE LIGHT EMITTING DIODE, MANUFACTURING METHOD FOR AN END FACET LIGHT EMITTING TYPE LIGHT EMITTING DEVICE AND MEASURING METHOD FOR THE SAME	FUJIWARA, HIROYUKI
08687046	5866439	150	07/18/1996	METHOD OF FABRICATING AN END FACE LIGHT EMITTING TYPE LIGHT-EMITTING DIODE AND A LIGHT-EMITTING DIODE ARRAY DEVICE	FUJIWARA, HIROYUKI
08701348	5862086	150	08/22/1996	SEMICONDUCTOR STORAGE DEVICE	FUJIWARA, HIROYUKI
08762417	5869848	150	12/09/1996	END FACE LIGHT-EMITTING-TYPE LED, END FACE LIGHT-EMITTING-TYPE LED ARRAY AND METHODS	FUJIWARA, HIROYUKI

				OF MANUFACTURING THEM	
<u>08894356</u>	7105719	150	08/18/1997	GENE ENCODING A PROTEIN HAVING ACYL GROUP TRANSFER ACTIVITY	FUJIWARA, HIROYUKI
<u>08942302</u>	5955748	150	10/01/1997	END FACE LIGHT EMITTING TYPE LIGHT EMITTING DIODE	FUJIWARA, HIROYUKI
<u>09562340</u>	6291328	150	05/01/2000	Opto-electronic device with self-aligned ohmic contact layer	FUJIWARA, HIROYUKI
<u>09933341</u>	6541796	150	08/20/2001	OPTO-ELECTRONIC DEVICE WITH SELF-ALIGNED OHMIC CONTACT LAYER	FUJIWARA, HIROYUKI
<u>09966598</u> Mo DP	Not Issued	161	10/01/2001	Electronic commercial transaction system, and server, user terminal and record medium for the system, and stock management method	FUJIWARA, HIROYUKI
<u>10312404</u>	6910514	150	03/06/2003	PART FEEDER	FUJIWARA, HIROYUKI
<u>10373404</u>	6765235	150	02/25/2003	ARRAY OF SEMICONDUCTOR ELEMENTS WITH PAIRED DRIVING SCHEME	FUJIWARA, HIROYUKI
<u>10374081</u>	6909122	150	02/27/2003	SEMICONDUCTOR LIGHT-EMITTING DEVICE WITH ISOLATION TRENCHES, AND METHOD OF FABRICATING SAME	FUJIWARA, HIROYUKI
<u>10631893</u>	6781246	150	08/01/2003	SEMICONDUCTOR ARRAY DEVICE WITH SINGLE INTERCONNECTION LAYER	FUJIWARA, HIROYUKI
<u>10701622</u>	Not Issued	93	11/06/2003	SEMICONDUCTOR APPARATUS WITH THIN SEMICONDUCTOR FILM	FUJIWARA, HIROYUKI
<u>10705895</u> Mo DP	Not Issued	41	11/13/2003	Combined semiconductor apparatus with thin semiconductor films	FUJIWARA, HIROYUKI
<u>10716601</u>	6790695	150	11/20/2003	SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME	FUJIWARA, HIROYUKI
<u>10734620</u>	7135708	150	12/15/2003	SEMICONDUCTOR APPARATUS HAVING CONDUCTIVE LAYERS AND SEMICONDUCTOR THIN FILMS	FUJIWARA, HIROYUKI
<u>10734676</u>	7122834	150	12/15/2003	SEMICONDUCTOR APPARATUS HAVING ADHESION LAYER AND SEMICONDUCTOR THIN FILM	FUJIWARA, HIROYUKI
<u>10743104</u> Mo DP	Not Issued	71	12/23/2003	Combined semiconductor apparatus with semiconductor thin film	FUJIWARA, HIROYUKI
<u>10870142</u>	6913985	150	06/18/2004	METHOD OF MANUFACTURING A	FUJIWARA,

				SEMICONDUCTOR DEVICE	HIROYUKI
10887699	7065269	150	07/09/2004	OPTICAL MULTIPLEXER/DEMULTIPLEXER, OPTICAL INTEGRATED CIRCUIT AND LIGHT TRANSCEIVER USING THE SAME	FUJIWARA, HIROYUKI
10900281 no DP	Not Issued	80	07/28/2004	Semiconductor light-emitting device	FUJIWARA, HIROYUKI
10926890	7061113	150	08/26/2004	SEMICONDUCTOR APPARATUS, LED HEAD, AND IMAGE FORMING APPARATUS	FUJIWARA, HIROYUKI
10936701	7078729	150	09/09/2004	SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME	FUJIWARA, HIROYUKI
10970637 no DP	Not Issued	71	10/21/2004	Semiconductor device, LED print head and image-forming apparatus using same, and method of manufacturing semiconductor device	FUJIWARA, HIROYUKI
10998801 no DP	Not Issued	71	11/30/2004	Semiconductor apparatus, LED print head, and printer	FUJIWARA, HIROYUKI
11037221	7131478	150	01/19/2005	COMPONENT SUPPLY SYSTEM	FUJIWARA, HIROYUKI
11119805 no DP	Not Issued	30	05/03/2005	Semiconductor light-emitting device with isolation trenches, and method of fabricating same	FUJIWARA, HIROYUKI
11268556 no DP	Not Issued	30	11/08/2005	Semiconductor composite apparatus, method for manufacturing the semiconductor composite apparatus, LED head that employs the semiconductor composite apparatus, and image forming apparatus that employs the LED head	FUJIWARA, HIROYUKI
11317800	Not Issued	25	12/22/2005	Bracket angle adjustment mechanism	FUJIWARA, HIROYUKI
11363292 no DP	Not Issued	41	02/23/2006	Semiconductor device, LED print head, that uses the semiconductor, and image forming apparatus that uses the LED print head	FUJIWARA, HIROYUKI
11385699 no DP	Not Issued	30	03/22/2006	Semiconductor composite apparatus, print head, and image forming apparatus	FUJIWARA, HIROYUKI
11445241 no DP	Not Issued	20	06/02/2006	Semiconductor device and method of manufacturing the same	FUJIWARA, HIROYUKI
11535132 no DP	Not Issued	25	09/26/2006	COMPOSITE SEMICONDUCTOR DEVICE, PRINT HEAD AND IMAGE FORMING APPARATUS	FUJIWARA, HIROYUKI
11543843 no DP	Not	30	10/06/2006	Semiconductor apparatus having	FUJIWARA,

Issued

conductive layers and semiconductor thin
films

HIROYUKI

Inventor Search Completed: No Records to Display.**Search Another: Inventor****Last Name**

fujiwara

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hiroyuki

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Last Name = SAKUTA

First Name = MASAAKI

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>10332942</u> <i>Mo DP</i>	Not Issued	30	01/13/2003	Working process administering system and method	SAKUTA, MASAAKI
<u>10701622</u> <i>Mo DP</i>	Not Issued	93	11/06/2003	SEMICONDUCTOR APPARATUS WITH THIN SEMICONDUCTOR FILM	SAKUTA, MASAAKI
<u>10705895</u> <i>Mo DP</i>	Not Issued	41	11/13/2003	Combined semiconductor apparatus with thin semiconductor films	SAKUTA, MASAAKI
<u>10734676</u>	<u>7122834</u>	150	12/15/2003	SEMICONDUCTOR APPARATUS HAVING ADHESION LAYER AND SEMICONDUCTOR THIN FILM	SAKUTA, MASAAKI
<u>10743104</u>	Not Issued	71	12/23/2003	Combined semiconductor apparatus with semiconductor thin film	SAKUTA, MASAAKI
<u>10870142</u>	<u>6913985</u>	150	06/18/2004	METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE	SAKUTA, MASAAKI
<u>10936515</u> <i>Mo DP</i>	Not Issued	40	09/09/2004	Combined semiconductor device, LED print head, and image forming apparatus	SAKUTA, MASAAKI
<u>10970637</u> <i>Mo DP</i>	Not Issued	71	10/21/2004	Semiconductor device, LED print head and image-forming apparatus using same, and method of manufacturing semiconductor device	SAKUTA, MASAAKI
<u>10998801</u> <i>Mo DP</i>	Not Issued	71	11/30/2004	Semiconductor apparatus, LED print head, and printer	SAKUTA, MASAAKI
<u>11268556</u> <i>Mo DP</i>	Not Issued	30	11/08/2005	Semiconductor composite apparatus, method for manufacturing the semiconductor composite apparatus, LED head that employs the semiconductor composite apparatus, and image forming apparatus that employs the LED head	SAKUTA, MASAAKI

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